TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

f_T

High f_T, low output capacitance, low base time constant and high gain, excellent noise characteristics.

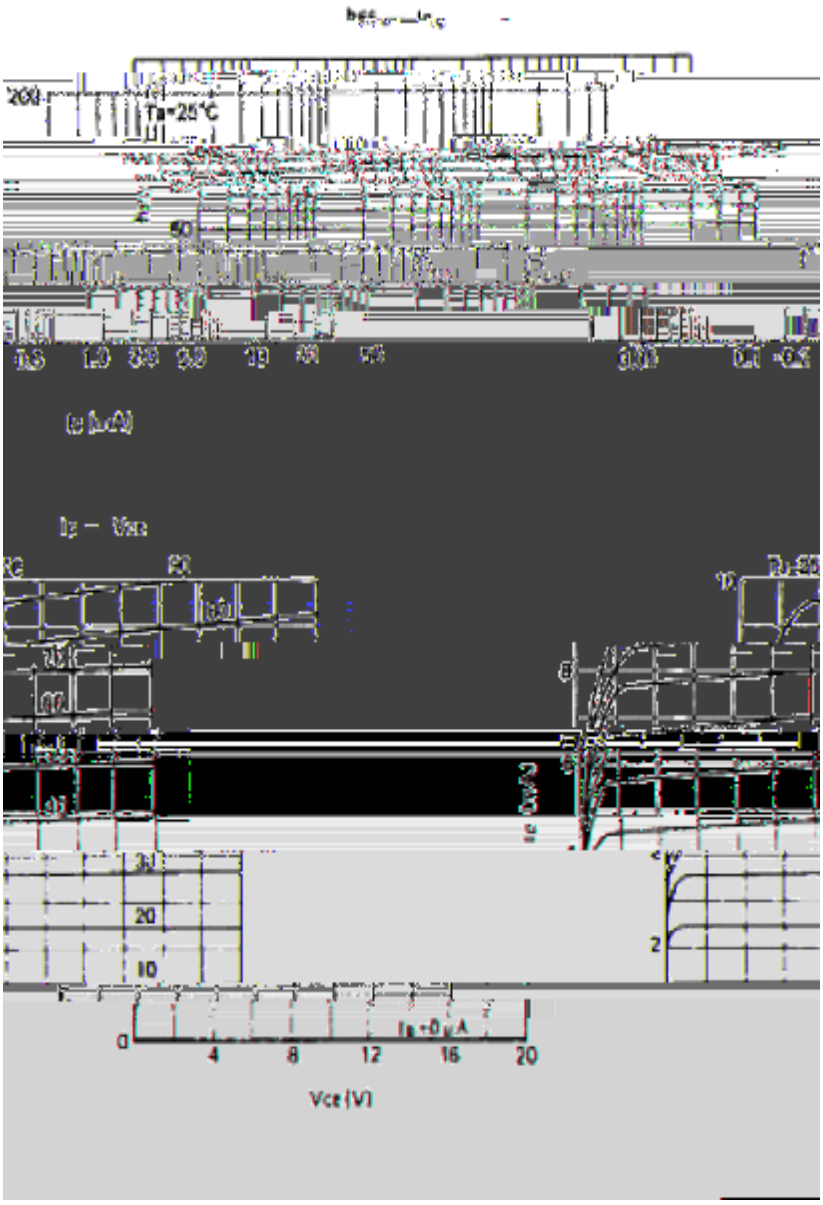
FM radio RF amplifier applications.

PIN1

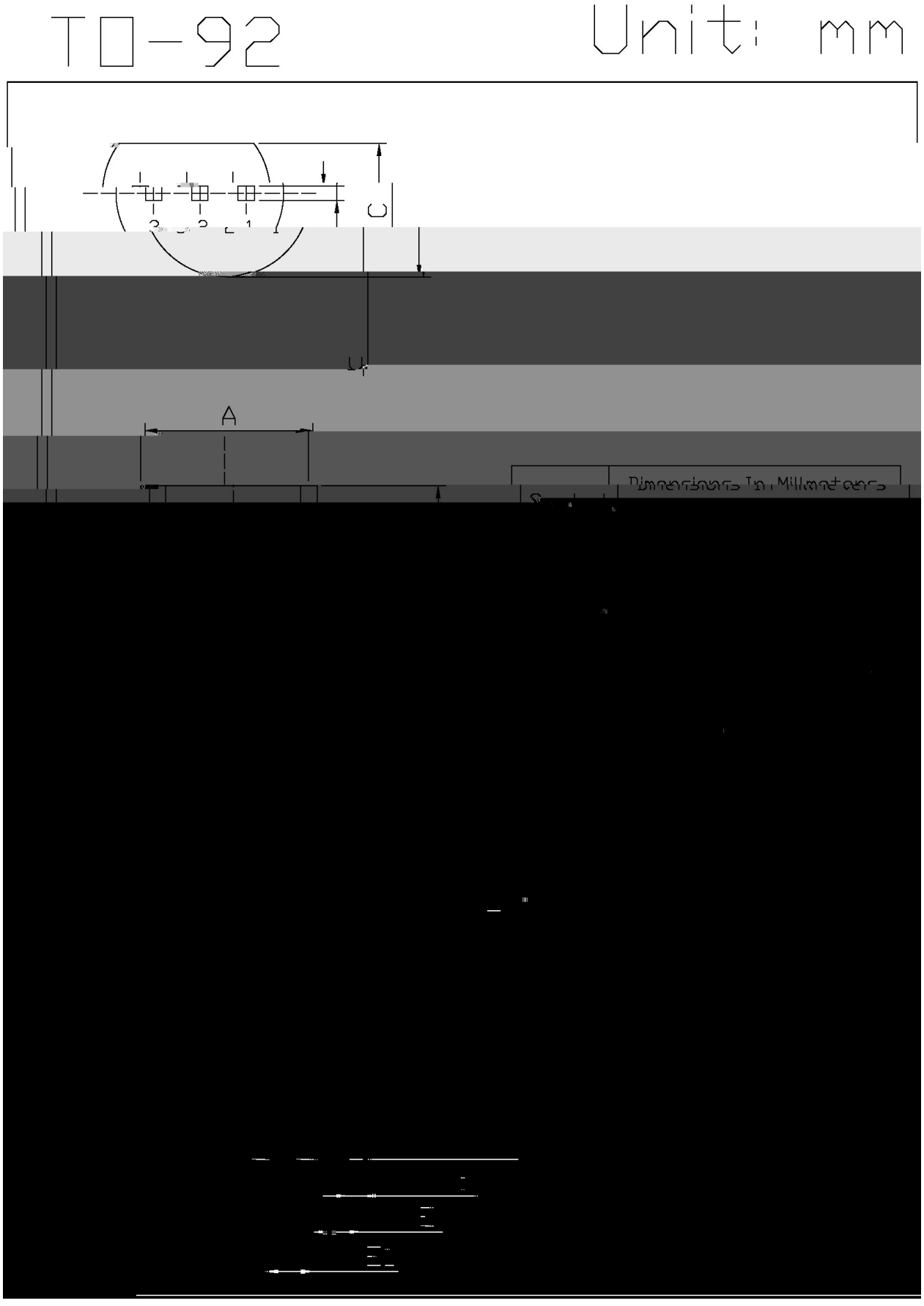
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	25	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	4.0	V
Collector Current - Continuous	I_C	20	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=10 A	25			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA	20			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=10 A	4.0			V
Collector Cut-Off Current	Colle5410.5 0 0 166.34 449.7803 Tm0 Tc(I)Tj0.003 Tw[C2 230.04 398.9603 Tm-0.001					

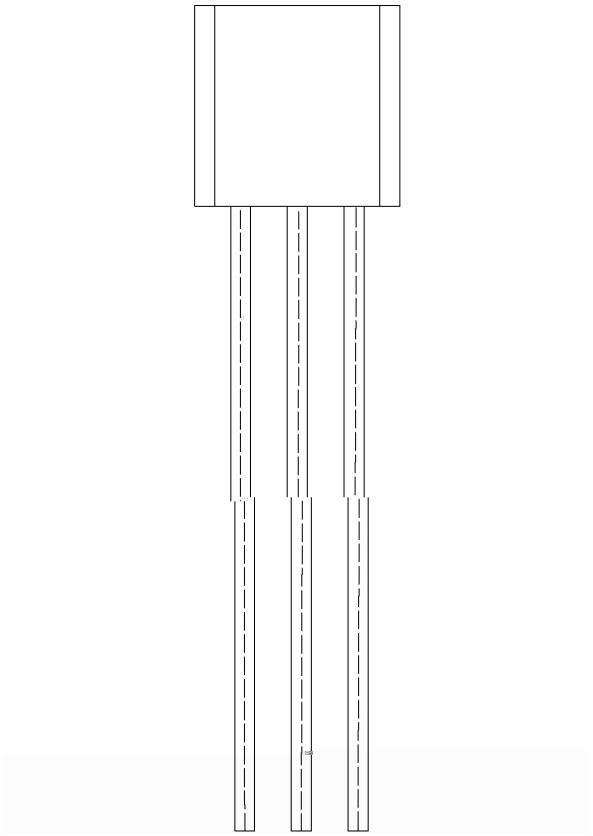
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR:

( ) / Temperature Profile for Dip Soldering(Pb-Free)

												Note:	
1		25		150			60		90sec;			1.Preheating:25~150 , Time:60~90sec.	
2		255±5							5±0.5sec;			2.Peak Temp.:255±5 , Duration:5±0.5sec.	
3						2		10	/sec.			3. Cooling Speed: 2~10 /sec.	

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量	Dimension 包装尺寸 (unit: mm3)